

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Gerrit Jan Hemink
Title: Self-Boosting System for Flash Memory Cells
Application No.: 10/774,014 Filing Date: February 6, 2004
Examiner: Unassigned Group Art Unit: 2827
Docket No.: SNDK.327US0 Conf. No.: 8419

Certificate of Mailing Under 37 CFR 1.8

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on March 28, 2005

Mary S. Bugger
Signature

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Pursuant to 37 C.F.R. §§ 1.56, 1.97 and 1.98, Applicant calls the documents listed on the enclosed Form PTO-1449 to the Examiner's attention in this patent application.

This application has a filing date after June 30, 2003. Therefore copies of the U.S. Patent and U.S. Published Patent Application documents listed on the accompanying Form PTO-1449 are not enclosed.

Citation of these documents shall not be construed as (1) an admission that the documents are prior art with respect to the invention or inventions claimed in this application, (2) a

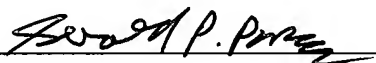
Attorney Docket No.: SNDK.327US0

Application No.: 10/774,014

representation that a search has been made (other than as indicated by any cited document), or
(3) an admission that the cited information is, or is considered to be, material to patentability as
defined in § 1.56(b).

This information disclosure statement is submitted under 37 C.F.R. § 1.97(b) and
consequently no fee should be required. The Commissioner is authorized, however, to charge
any fee that may be required, or to credit any overpayment, against Deposit Account No.
502664. This form is being submitted in duplicate.

Respectfully submitted,



Gerald P. Parsons
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March 28, 2005
Date

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U.S. Department of Commerce, Patent and Trademark				Atty. Docket No.		Application No.	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				SNDK.327US0		10/774,014	
				Applicant(s)		Conf. No.	
(Use several sheets if necessary)				Gerrit Jan Hemink		8419	
(Form PTO-1449)				Filing Date		Art Group	
				February 6, 2004		2827	

U.S. Patent Documents							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	1	5,043,940	8/27/1991	Harari			
	2	5,172,338	12/15/1992	Mehrotra et al.			
	3	5,570,315	10/29/1996	Tanaka et al.			
	4	5,774,397	6/30/1998	Endoh et al.			
	5	5,887,145	3/23/1999	Harari et al.			
	6	6,046,935	4/4/2000	Takeuchi et al.			
	7	6,107,658	8/22/2000	Itoh et al.			
	8	6,456,528	9/24/2002	Chen			
	9	6,522,580	2/18/2003	Chen et al.			
	10	6,525,964	2/25/2003	Tanaka et al.			

U.S. Published Patent Application Documents							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	11	2003/0147278A1	8/7/2003	Tanaka et al.			

Foreign Patent Documents								
							Translation	
		Document	Date	Country	Class	Subclass	Yes	No

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)	
12	Takaaki Nozaki et al., "A 1-Mb EEPROM with MONOS Memory Cell for Semiconductor Disk Application" IEEE Journal of Solid-State Circuits, Vol. 26, No. 4, April 1991, pp. 497-501.
13	K. D. Suh et al. in "A 3.3 V 32 Mb NAND Flash Memory with Incremental Step Pulse Programming Scheme," Journal of Solid-State Circuits, Vol 30, No. 11, Nov. 1995, pp. 1149-55.
14	T. S. Jung et al. proposed a local self boosting ("LSB") technique in "A 3.3V 128Mb Multi-Level NAND Flash Memory for Mass Storage Applications", ISSCC96, Session 2, Flash Memory, Paper TP 2.1, IEEE, pp. 32.

Examiner	Date Considered
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.